

Product Specification

XBLW AO3416A

N-Channel Enhancement Mode MOSFET











Description

The AO3416A uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

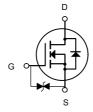
- \rightarrow VDS = 20V ID =6.5A
- \triangleright RDS(ON) < 22m Ω @ VGS=4.5V
- ➤ ESD=2500HBM

Application

- Battery protection
- Load switch
- Uninterruptible power supply



SOT-23-3L



N-Channel MOSFET

Package Marking and Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
XBLW AO3416A	SOT-23-3L	AGBV	Tape	3000Pcs/Reel

Absolute Maximum Ratings (TA=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	20	V
V _G s	Gate-Source Voltage	±12	V
ID	Drain Current-Continuous	6.5	Α
Ідм	Drain Current-Pulsed (Note 1)	30	А
P _D	Maximum Power Dissipation	1.4	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	89	°C/W



Electrical Characteristics (TA=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20		-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±10V,V _{DS} =0V	-	-	±10	μA
Gate Threshold Voltage	VGS(th)	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.45	0.7	1.0	V
		V _{GS} =4.5V, I _D =6.5A	-	14	22	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =2.5V, I _D =5.5A	-	17	26	mΩ
		V _{GS} =1.8V, I _D =5A	-	28	40	mΩ
Forward Transconductance	gFS	V _{DS} =5V,I _D =6.5A	8	-	-	S
Input Capacitance	Clss		-	660	-	PF
Output Capacitance	Coss	V_{DS} =10V, V_{GS} =0V, F=1.0MHz	-	160	-	PF
Reverse Transfer Capacitance	Crss	1 – 1.0WH12	-	87	-	PF
Turn-on Delay Time	t _{d(on)}		-	0.5		nS
Turn-on Rise Time	t _r	V _{DD} =10V,R _L =1. 5Ω	-	1		nS
Turn-Off Delay Time	td(off)	V_{GS} =5 V , R_{GEN} =3 Ω	-	12		nS
Turn-Off Fall Time	t _f		-	4		nS
Total Gate Charge	Qg		-	8		nC
Gate-Source Charge	Qgs	V_{DS} =10V, I_{D} =6.5A, V_{GS} =4.5V	-	2.5	-	nC
Gate-Drain Charge	Q _{gd}			3	-	nC
Diode Forward Voltage (Note 3)	Vsp	V _{GS} =0V,I _S =6.5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6.5	Α

Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature. Surface Mounted on FR4 Board, $t \leq 10$ sec. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. Guaranteed by design, not subject to production



Typical Characteristics

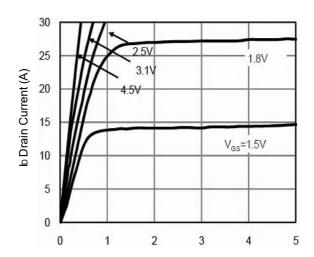


Fig.1 Typical Output Characteristics

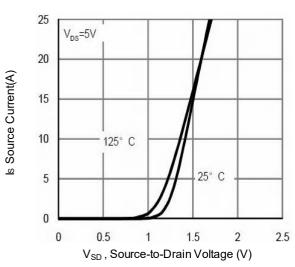


Fig.3 Forward Characteristics of Reverse

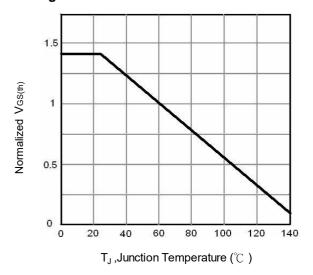


Fig.5 Normalized V_{GS(th)} vs. T_J

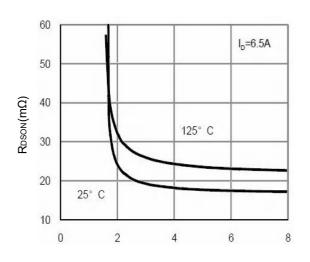


Fig.2 On-Resistance vs. Gate-Source

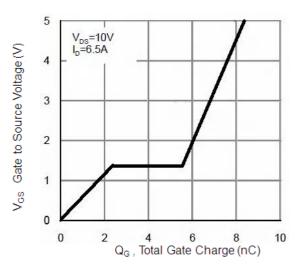


Fig.4 Gate-Charge Characteristics

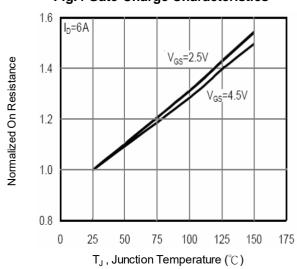
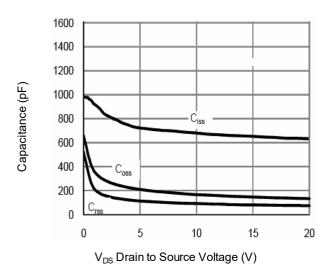


Fig.6 Normalized R_{DSON} vs. T_J





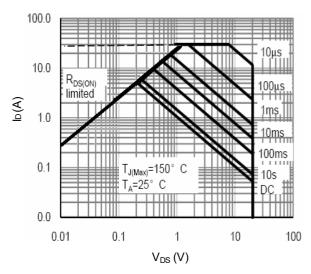
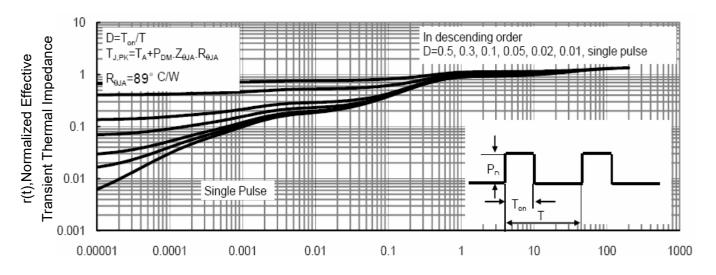
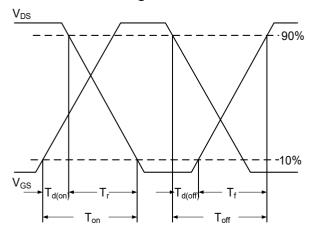


Fig.7 Capacitance

Fig.8 Safe Operating Area



Square Wave Pluse Duration(sec)
Fig.9 Normalized Maximum Transient Thermal Impedance



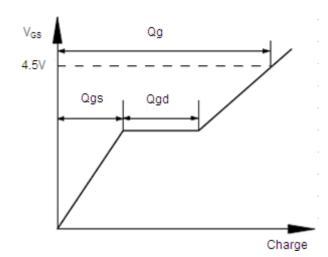


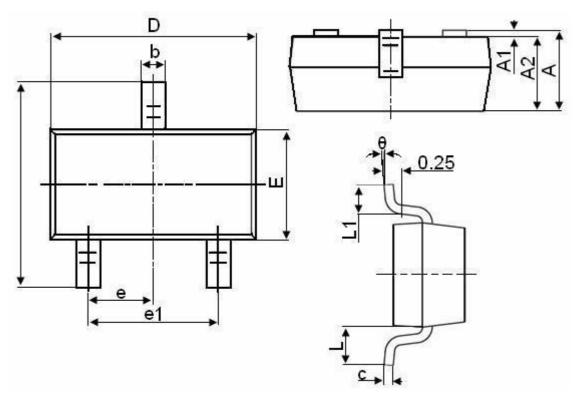
Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform



Package Information

SOT23 3L



Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
А	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.800	3.000		
E	1.500	1.700		
E1	2.650	2.950		
е		0.950TYP		
e1	1.800	2.000		
L		0.550REF		
L1	0.300	0.600		
θ	0°	8°		



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